

EAST - [fig.wsp:1]

FileViewEditToolsWindowHelp

Active

L1: (33216) gate and floating and control

L2: (16657) 1 and gate.clm.

L3: (6379) 2 and flash

L4: (5286) 3 and (floating or control).clm.

L5: (4423) 4 and (tunnel or oxide)

L6: (2494) 5 and dielectric

L7: (1363) 6 and oxidation

L8: (13) 7 and (dry adj oxidis5)

L9: (7) 8 and ((sidewall\$1) or (side adj wall\$1))

L10: (0) 5 and C\$1H\$1C1\$1

L11: (20) 5 and (dry adj oxidis4)

L12: (13) 11 and (sidewall or (side adj wall))

L13: (0) 5 and oxygen and TCA

L14: (15712) silicon adj germanium or (SiGe)

L15: (5830) 14 and plasma

L16: (2489) 15 and (hydrogen or H\$1)and (Ar or argon)

Print

Find

Browse

Queue

Clear

DB: USPAT:US-PCPUG

Default operator: OR

22 and (H\$1 or hydrogen).clm. and (argon.clm. or Ar.clm.)

US\$ term

US\$ term

US\$ term

US\$ term

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US\$ term

	V	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval C	Inventor	S	C	P	3	Ina
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20010013607 A1	20010816	35	FABRICATION METHOD FOR A THIN FILM SEMICONDUCTOR DEVI	257/66	257/72; 257/E21.101;		MIYASAKA, MITSUTOSHI	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2001
2	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6187682 B1	20010213	15	Inert plasma gas surface cleaning process performed i	438/694	204/192.3; 257/E21.165;		Denning, Dean J. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6017779 A	20000125	32	Fabrication method for a thin film semiconductor devi	438/149	257/E21.101; 257/E21.202;		Miyasaka, Mitsutoshi	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6

Hit

Details

HTML

Ready

NUM